SILICON RF SWITCHING DIODE

Features

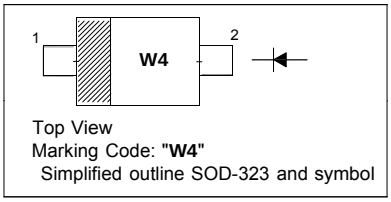
- Very low forward resistance
- Small capacitance

Applications

- For band switching in TV/VTR tuners and mobile applications

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View
Marking Code: "**W4**"
Simplified outline SOD-323 and symbol

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Diode Reverse Voltage	V_R	35	V
Forward Current	I_F	100	mA
Junction Temperature	T_J	150	°C
Operating Temperature Range	T_{op}	- 55 to + 125	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Electrical Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Typ.	Max.	Unit
Reverse Current at V_R = 20 V	I_R	-	-	20	nA
Forward Voltage at I_F = 100 mA	V_F	-	-	1	V
Diode Capacitance at V_R = 1 V, f = 1 MHz at V_R = 3 V, f = 1 MHz	C_T	0.65 0.6	- -	1.4 1.1	pF
Reverse Parallel Resistance at V_R = 0 V, f = 100 MHz	R_P	-	100	-	KΩ
Forward Resistance at I_F = 3 mA, f = 100 MHz at I_F = 10 mA, f = 100 MHz	r_f	- -	- -	0.7 0.5	Ω
Series Inductance	L_s	-	1.8	-	nH

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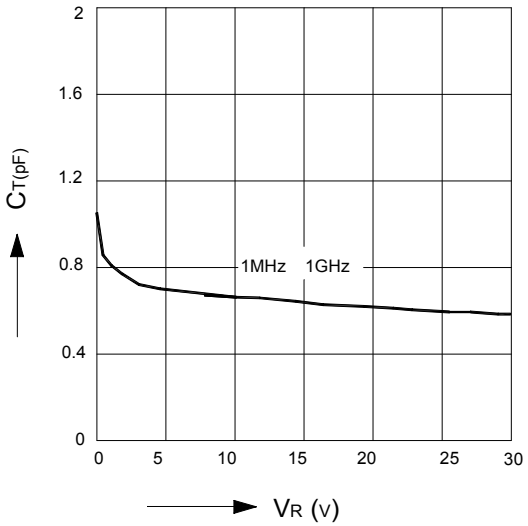
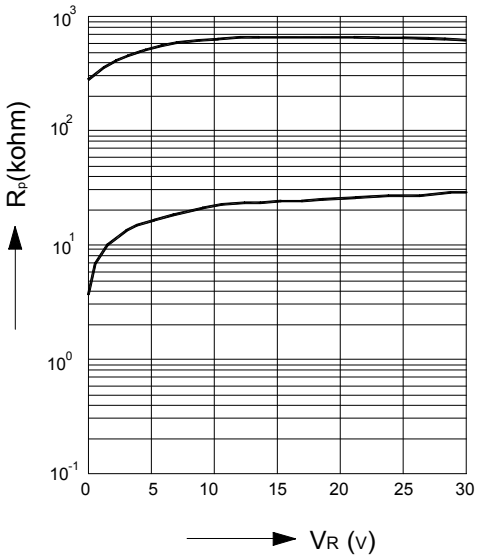
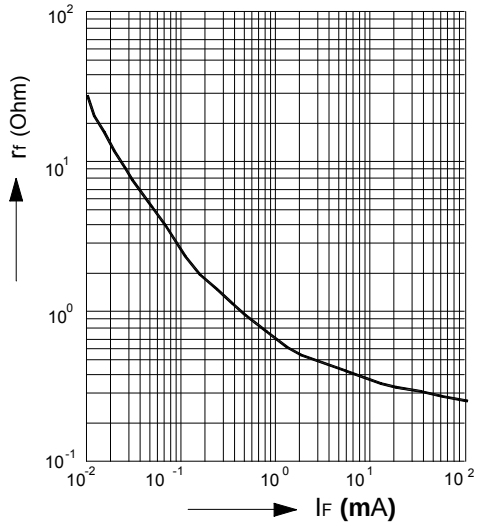
Diode capacitance $C_T=f(V_R)$
f=Parameter



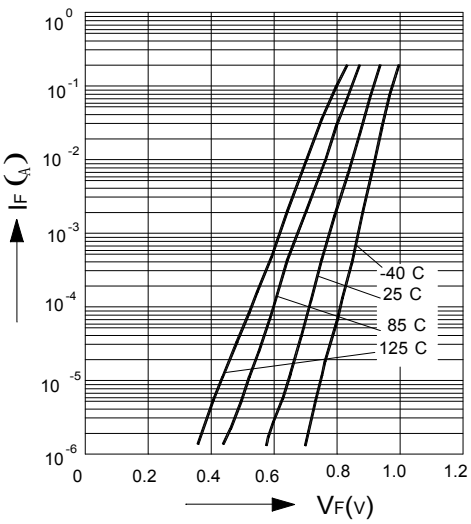
Reverse current $R_P=f(V_R)$
f=Parameter



Forward resistance $r_f=f(I_F)$
f=100MHz



Forward current $I_F=f(V_F)$
T_A=Parameter



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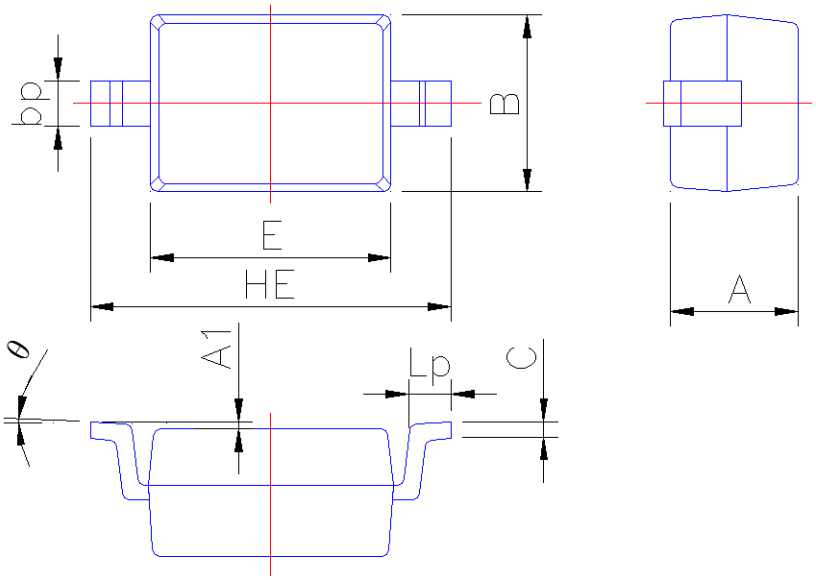
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-323**



Symbol	Dimension in Millimeters	
	Min	Max
A	0.95	1.15
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.40
C	0.09	0.150
E	1.60	1.80
HE	2.30	2.70
Lp	0.20	0.40
θ	0°	5°

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